

TOSHIBA Diode Silicon Epitaxial Planar Type

1SS337

Ultra High Speed Switching Application

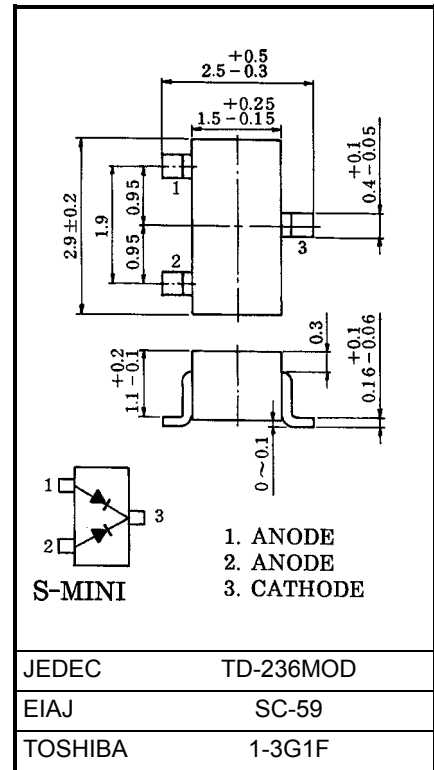
- Small package : SC-59
- Low forward voltage : $V_F(3) = 0.88V$ (typ.)
- Fast reverse recovery time: $t_{rr} = 6ns$ (typ.)
- Small total capacitance : $C_T = 1.6pF$ (typ.)

Maximum Ratings ($T_a = 25^\circ C$)

Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V_{RM}	85	V
Reverse voltage	V_R	80	V
Maximum (peak) forward current	I_{FM}	600 *	mA
Average forward current	I_O	200 *	mA
Surge current (10ms)	I_{FSM}	6 *	A
Power dissipation	P	150	mW
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55~150	$^\circ C$

*: Unit rating. Total rating = unit rating \times 1.5

Unit in mm



Weight: 0.012g

Electrical Characteristics ($T_a = 25^\circ C$)

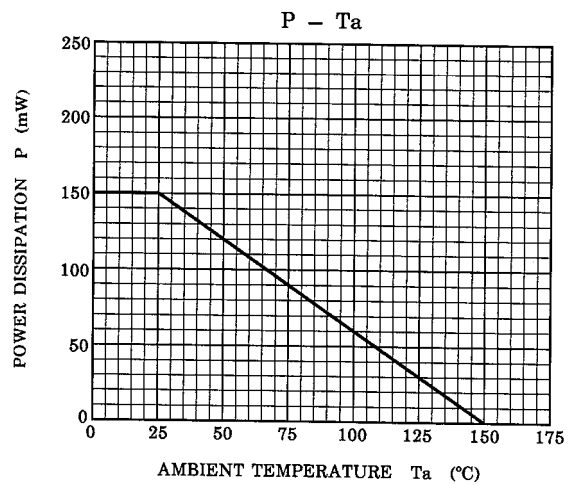
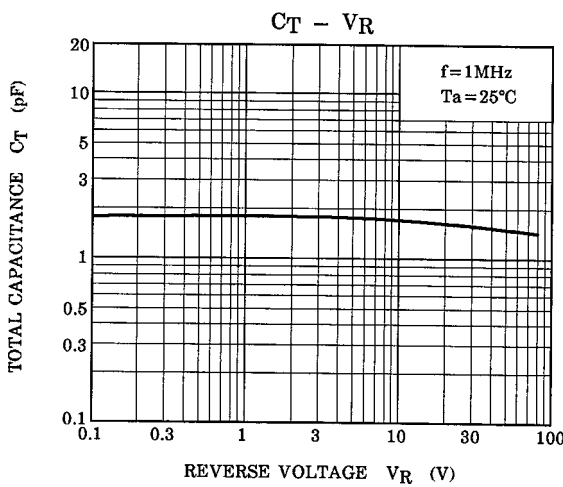
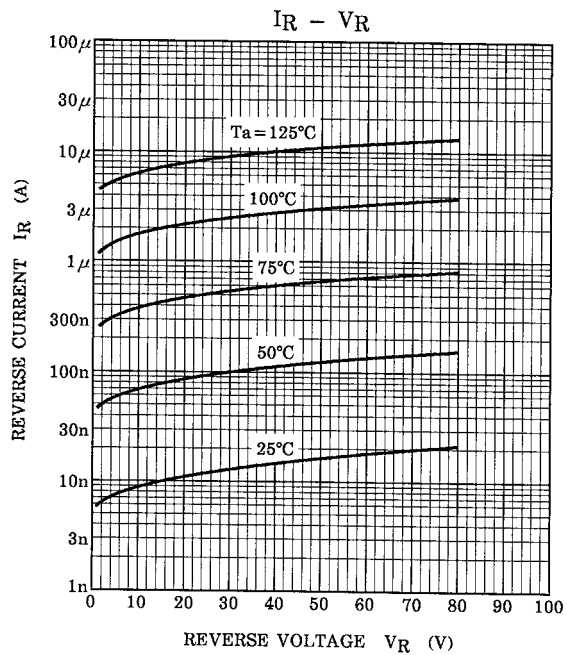
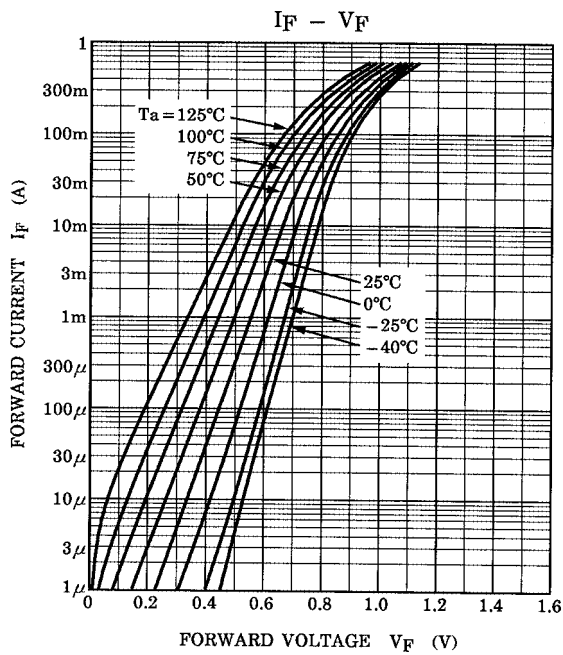
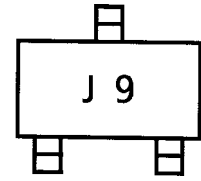
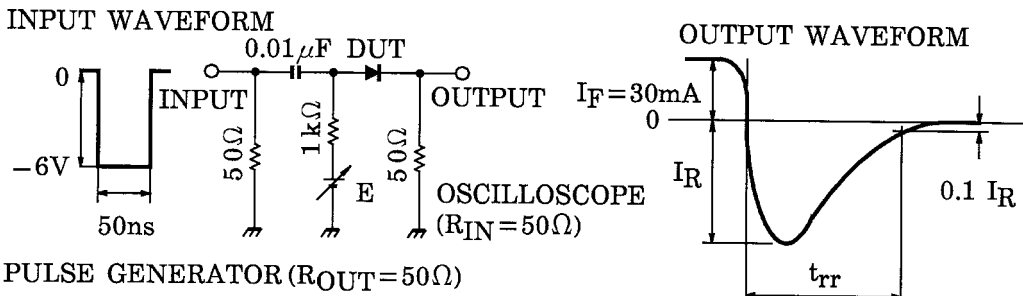
Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Forward voltage	$V_F(1)$	—	$I_F = 10mA$	—	0.66	—	V
	$V_F(2)$	—	$I_F = 100mA$	—	0.80	—	
	$V_F(3)$	—	$I_F = 200mA$	—	0.88	1.20	
Reverse current	$I_R(1)$	—	$V_R = 30V$	—	—	0.25	μA
	$I_R(2)$	—	$V_R = 80V$	—	—	0.50	
Total capacitance	C_T	—	$V_R = 0, f = 1MHz$	—	1.6	—	pF
Reverse recovery time	t_{rr}	—	$I_F = 30mA, Fig.1$	—	6	20	ns

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Fig.1 Reverse Recovery Time (t_{rr}) Test Circuit

Marking



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